

Description

The HXY4828S uses advanced trench technology to provide excellent R_{DS(ON)}, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

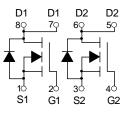
 $V_{DS} = 60V \ I_D = 6.5 \ A$ $R_{DS(ON)} < 36m\Omega @ V_{GS} = 10 \ V$ $R_{DS(ON)} < 48m\Omega @ V_{GS} = 4.5 \ V$

Application

Battery protection Load switch Uninterruptible power supply



SOP-8



Dual N-Channel MOSFET

Package Marking and Ordering Information

| Product ID | Pack | Marking | Qty(PCS) |
|------------|-------|---------------|----------|
| HXY4828S | SOP-8 | 4828 XXX YYYY | 3000 |

Absolute Maximum Ratings@Tj=25°C(unless otherwise specified)

| Symbol | Parameter | Rating | Units | |
|-------------------------------------|---------------------------------------------------------------|-------------|-------|--|
| V _{DS} | Drain-Source Voltage | 60 | V | |
| V _{GS} | Gate-Source Voltage | <u>+</u> 20 | V | |
| I₀@T₄=25℃ | Drain Current, V _{GS} @ 4.5V ³ | 6.5 | Α | |
| I₀@T₄=70°C | Drain Current, V _{GS} @ 4.5V ³ | 5 | A | |
| Ідм | Pulsed Drain Current ¹ | 30 | A | |
| P _D @T _A =25℃ | Total Power Dissipation | 2.1 | W | |
| Тѕтс | Storage Temperature Range | -55 to 150 | °C | |
| TJ | Operating Junction Temperature Range | -55 to 150 | °C | |
| Rthj-a | Maximum Thermal Resistance, Junction- ambient ³ | 60 | °C/W | |



Dual N-Channel Enhancement Mode MOSFET

Electrical Characteristics (T_A=25 $^{\circ}$ C unless otherwise noted)

| Parameter | Symbol | Condition | Min | Тур | Max | Unit |
|------------------------------------|---------------------|----------------------------------------------------------------------|-----|------|------|------|
| Off Characteristics | | | • | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | V _{GS} =0V I _D =250µA | 60 | | - | V |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} =60V,V _{GS} =0V | - | | 1 | μA |
| Gate-Body Leakage Current | I _{GSS} | $V_{GS}=\pm 20V, V_{DS}=0V$ | - | - | ±100 | nA |
| On Characteristics (Note 3) | | | • | | | |
| Gate Threshold Voltage | V _{GS(th)} | $V_{DS}=V_{GS}$, $I_{D}=250\mu A$ | 1.0 | 1.4 | 2.0 | V |
| | R _{DS(ON)} | V _{GS} =10V, I _D =6A | | 32 | 36 | mΩ |
| Drain-Source On-State Resistance | | V _{GS} =4.5V, I _D =4A | | 34 | 48 | mΩ |
| Forward Transconductance | g fs | V _{DS} =5V,I _D =6A | | 20 | - | S |
| Dynamic Characteristics (Note4) | L L | | | | | |
| Input Capacitance | Clss | N/ 051/11/ 01/ | | 1920 | | PF |
| Output Capacitance | Coss | $V_{DS}=25V, V_{GS}=0V,$ | | 155 | | PF |
| Reverse Transfer Capacitance | C _{rss} | F=1.0MHz | | 116 | | PF |
| Switching Characteristics (Note 4) | | | | | | |
| Turn-on Delay Time | t _{d(on)} | | - | 8 | - | nS |
| Turn-on Rise Time | t _r | V_{DS} =30V, R _L =4.7 Ω | - | 5 | - | nS |
| Turn-Off Delay Time | t _{d(off)} | V_{GS} =10V, R_{GEN} =3 Ω | - | 29 | - | nS |
| Turn-Off Fall Time | t _f | | - | 6 | - | nS |
| Total Gate Charge | Qg | N/ 201/1 CA | - | 50 | - | nC |
| Gate-Source Charge | Q _{gs} | V _{DS} =30V,I _D =6A, V _{GS} =10V | - | 8 | - | nC |
| Gate-Drain Charge | Q _{gd} | V _{GS} -10V | - | 16 | - | nC |
| Drain-Source Diode Characteristic | cs | | | | | |
| Diode Forward Voltage (Note 3) | V _{SD} | V _{GS} =0V,I _S =6A | - | - | 1.2 | V |
| Diode Forward Current (Note 2) | Is | | - | - | 7 | Α |
| Reverse Recovery Time | t _{rr} | TJ = 25°C, I _F =7A | - | 35 | - | nS |
| Reverse Recovery Charge | Qrr | $di/dt = 100A/\mu s^{(Note3)}$ | - | 43 | - | nC |
| Forward Turn-On Time | t _{on} | Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD) | | | |) |

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

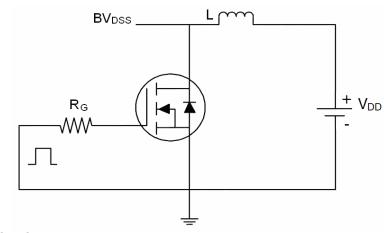
2. Surface Mounted on FR4 Board, $t \le 10$ sec.

3. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

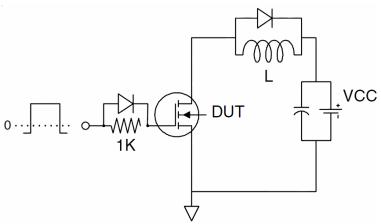
4. Guaranteed by design, not subject to production



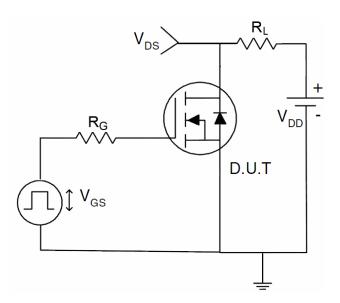
Test Circuit 1) E_{AS} test Circuits



2) Gate charge test Circuit

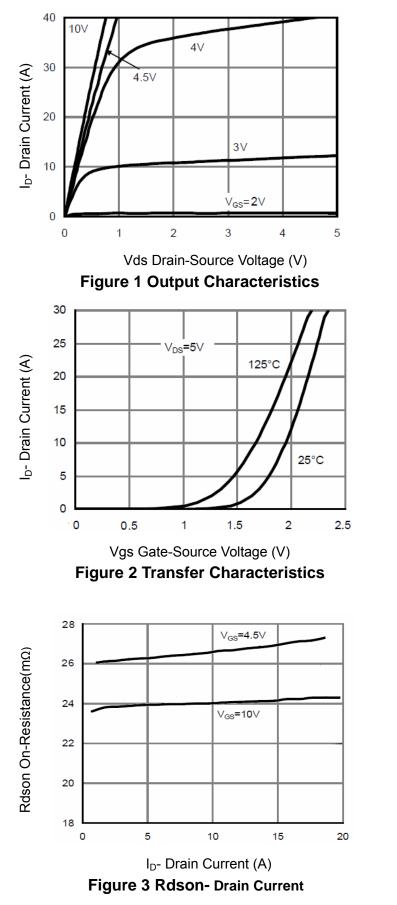


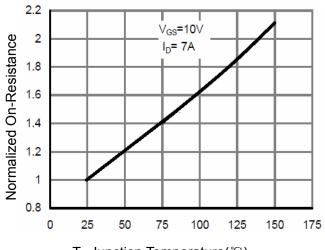
3) Switch Time Test Circuit





Typical Electrical and Thermal Characteristics (Curves)





 $\mathsf{T}_{\mathsf{J}} ext{-}\mathsf{Junction}$ Temperature($^{\circ}\!\!\mathbb{C}$)

Figure 4 Rdson-JunctionTemperature

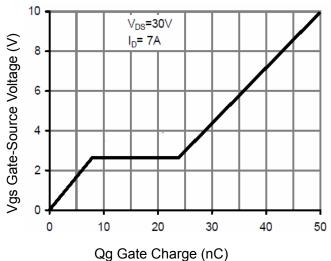


Figure 5 Gate Charge

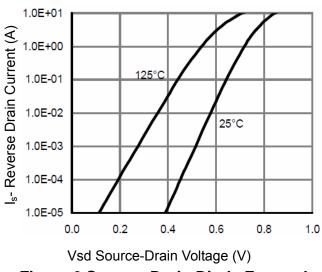
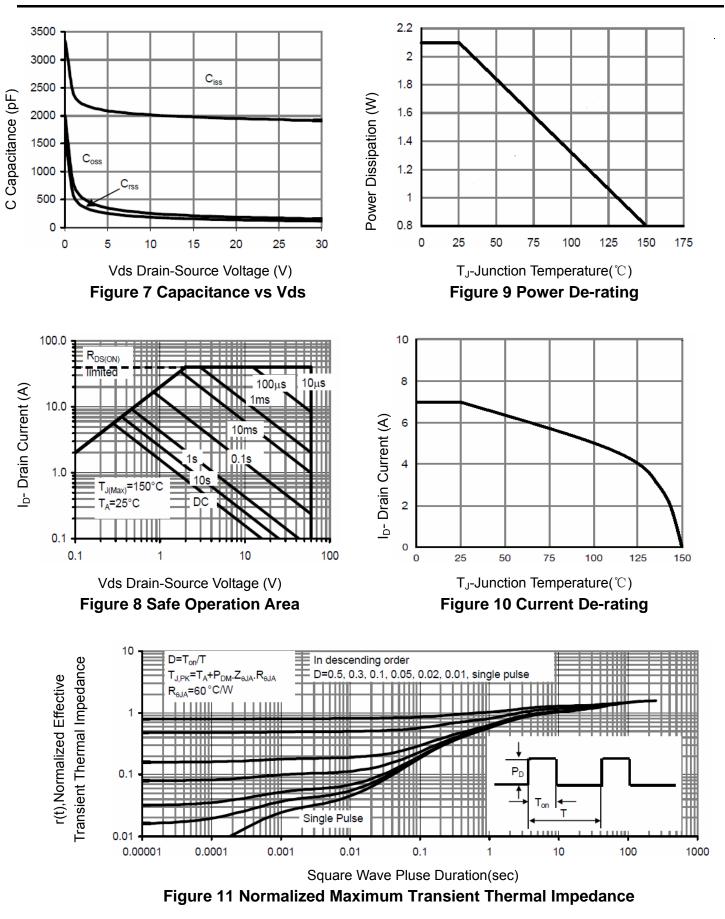


Figure 6 Source- Drain Diode Forward

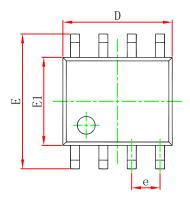


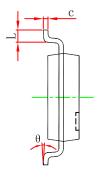
HXY4828S Dual N-Channel Enhancement Mode MOSFET

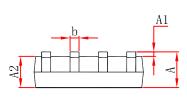




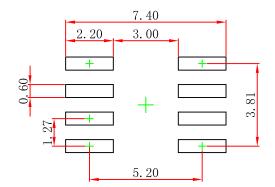
SOP-8 Package Outline Dimensions







| Symbol | Dimensions In Millimeters | | Dimensions In Inches | | |
|--------|---------------------------|-------|----------------------|-------|--|
| | Min | Max | Min | Max | |
| А | 1.350 | 1.750 | 0.053 | 0.069 | |
| A1 | 0.100 | 0.250 | 0.004 | 0.010 | |
| A2 | 1.350 | 1.550 | 0.053 | 0.061 | |
| b | 0.330 | 0.510 | 0.013 | 0.020 | |
| с | 0.170 | 0.250 | 0.007 | 0.010 | |
| D | 4.800 | 5.000 | 0.189 | 0.197 | |
| e | 1.270 (BSC) | | 0.050 (BSC) | | |
| E | 5.800 | 6.200 | 0.228 | 0.244 | |
| E1 | 3.800 | 4.000 | 0.150 | 0.157 | |
| L | 0.400 | 1.270 | 0.016 | 0.050 | |
| θ | 0 ° | 8° | 0 ° | 8° | |



Note: 1.Controlling dimension:in millimeters.

2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only.



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